

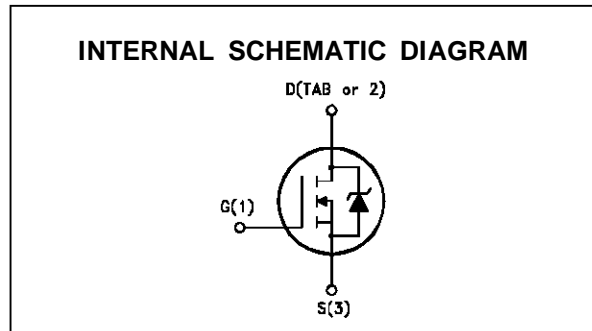
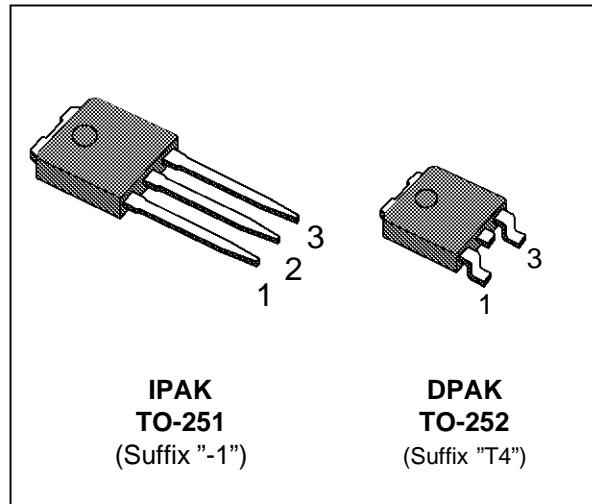
N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTOR

| TYPE | V _{DSS} | R _{DS(on)} | I _D |
|---------|------------------|---------------------|----------------|
| STD2N50 | 500 V | < 5.5 Ω | 2 A |

- TYPICAL R_{DS(on)} = 4.5 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- APPLICATION ORIENTED CHARACTERIZATION
- THROUGH-HOLE IPAK (TO-251) POWER PACKAGE IN TUBE (SUFFIX "-1")
- SURFACE-MOUNTING DPAK (TO-252) POWER PACKAGE IN TAPE & REEL (SUFFIX "T4")

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- CHOPPER REGULATORS, CONVERTERS, MOTOR CONTROL, LIGHTING FOR INDUSTRIAL AND CONSUMER ENVIRONMENT



ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|---------------------|---|------------|------|
| V _{DS} | Drain-source Voltage (V _{GS} = 0) | 500 | V |
| V _{DGR} | Drain- gate Voltage (R _{GS} = 20 kΩ) | 500 | V |
| V _{GS} | Gate-source Voltage | ± 20 | V |
| I _D | Drain Current (continuous) at T _c = 25 °C | 2 | A |
| I _D | Drain Current (continuous) at T _c = 100 °C | 1.25 | A |
| I _{DM} (●) | Drain Current (pulsed) | 8 | A |
| P _{tot} | Total Dissipation at T _c = 25 °C | 45 | W |
| | Derating Factor | 0.36 | W/°C |
| T _{stg} | Storage Temperature | -65 to 150 | °C |
| T _j | Max. Operating Junction Temperature | 150 | °C |

(●) Pulse width limited by safe operating area

STD2N50

THERMAL DATA

| | | | | |
|----------------|--|-----|------|---------------|
| $R_{thj-case}$ | Thermal Resistance Junction-case | Max | 2.78 | $^{\circ}C/W$ |
| $R_{thj-amb}$ | Thermal Resistance Junction-ambient | Max | 100 | $^{\circ}C/W$ |
| $R_{thc-sink}$ | Thermal Resistance Case-sink | Typ | 1.5 | $^{\circ}C/W$ |
| T_l | Maximum Lead Temperature For Soldering Purpose | | 275 | $^{\circ}C$ |

AVALANCHE CHARACTERISTICS

| Symbol | Parameter | Max Value | Unit |
|----------|---|-----------|------|
| I_{AR} | Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max, $\delta < 1\%$) | 2 | A |
| E_{AS} | Single Pulse Avalanche Energy (starting $T_j = 25^{\circ}C$, $I_D = I_{AR}$, $V_{DD} = 50 V$) | 20 | mJ |
| E_{AR} | Repetitive Avalanche Energy (pulse width limited by T_j max, $\delta < 1\%$) | 1.5 | mJ |
| I_{AR} | Avalanche Current, Repetitive or Not-Repetitive ($T_c = 100^{\circ}C$, pulse width limited by T_j max, $\delta < 1\%$) | 1.2 | A |

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise specified)

OFF

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------|--|--|------|------|-----------|--------------------|
| $V_{(BR)DSS}$ | Drain-source Breakdown Voltage | $I_D = 250 \mu A$ $V_{GS} = 0$ | 500 | | | V |
| I_{DSS} | Zero Gate Voltage Drain Current ($V_{GS} = 0$) | $V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating} \times 0.8$ $T_c = 125^{\circ}C$ | | | 25 250 | μA μA |
| I_{GSS} | Gate-body Leakage Current ($V_{DS} = 0$) | $V_{GS} = \pm 20 V$ | | | ± 100 | nA |

ON (*)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|--------------|-----------------------------------|--|------|------|------|----------|
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS} = V_{GS}$ $I_D = 250 \mu A$ | 2 | 3 | 4 | V |
| $R_{DS(on)}$ | Static Drain-source On Resistance | $V_{GS} = 10V$ $I_D = 1 A$ | | 4.5 | 5.5 | Ω |
| $I_{D(on)}$ | On State Drain Current | $V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10 V$ | 2 | | | A |

DYNAMIC

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|--------------|------------------------------|---|------|------|------|------|
| g_{fs} (*) | Forward Transconductance | $V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 1 A$ | 0.65 | 1 | | S |
| C_{iss} | Input Capacitance | $V_{DS} = 25 V$ $f = 1 MHz$ $V_{GS} = 0$ | | 200 | 270 | pF |
| C_{oss} | Output Capacitance | | | 35 | 50 | pF |
| C_{rss} | Reverse Transfer Capacitance | | | 12 | 18 | pF |

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-------------------------------|--|---|------|--------------|-----------|----------------|
| $t_{d(on)}$ t_r | Turn-on Time Rise Time | $V_{DD} = 200\text{ V}$ $I_D = 1\text{ A}$ $R_G = 50\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 3) | | 35 85 | 50 120 | ns ns |
| $(di/dt)_{on}$ | Turn-on Current Slope | $V_{DD} = 400\text{ V}$ $I_D = 2\text{ A}$ $R_G = 50\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5) | | 28 | | A/ μ s |
| Q_g Q_{gs} Q_{gd} | Total Gate Charge Gate-Source Charge Gate-Drain Charge | $V_{DD} = 400\text{ V}$ $I_D = 2\text{ A}$ $V_{GS} = 10\text{ V}$ | | 18 5 8 | 25 | nC nC nC |

SWITCHING OFF

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------------------------|---|---|------|----------------|----------------|----------------|
| $t_{r(Voff)}$ t_f t_c | Off-voltage Rise Time Fall Time Cross-over Time | $V_{DD} = 400\text{ V}$ $I_D = 2\text{ A}$ $R_G = 50\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5) | | 25 15 45 | 35 25 65 | ns ns ns |

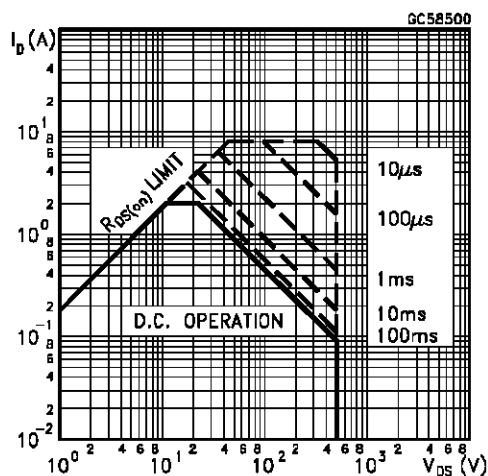
SOURCE DRAIN DIODE

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-----------------------------------|--|---|------|------------------|--------|--------------------|
| I_{SD} $I_{SDM}(\bullet)$ | Source-drain Current Source-drain Current (pulsed) | | | | 2 8 | A A |
| $V_{SD} (*)$ | Forward On Voltage | $I_{SD} = 2\text{ A}$ $V_{GS} = 0$ | | | 1.5 | V |
| t_{rr} Q_{rr} I_{RRM} | Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current | $I_{SD} = 2\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$ (see test circuit, figure 5) | | 330 2.5 15 | | ns μ C A |

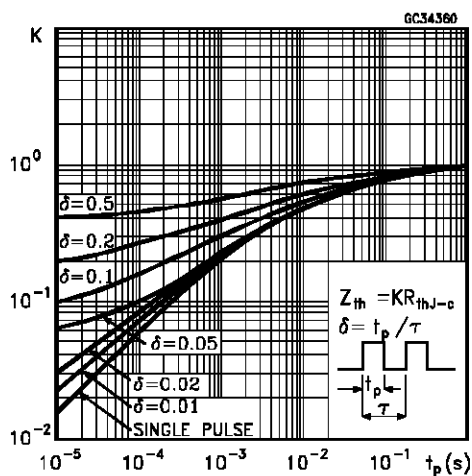
(*) Pulsed: Pulse duration = 300 μ s, duty cycle 1.5%

(\bullet) Pulse width limited by safe operating area

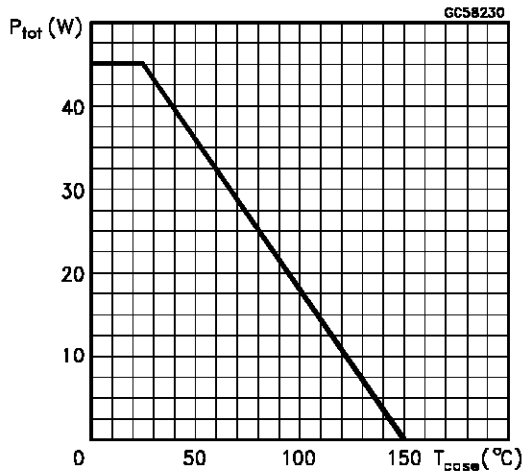
Safe Operating Area



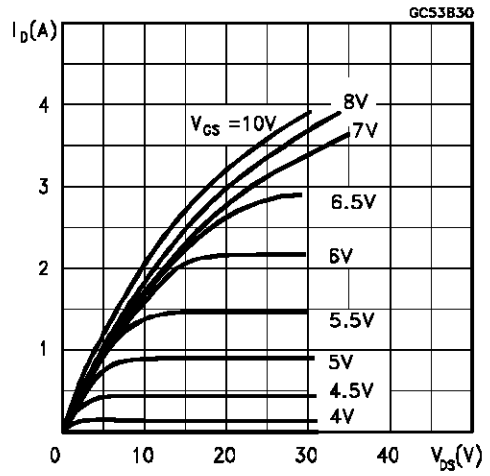
Thermal Impedance



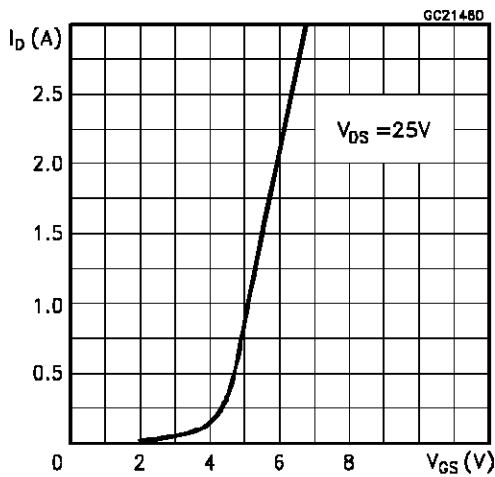
Derating Curve



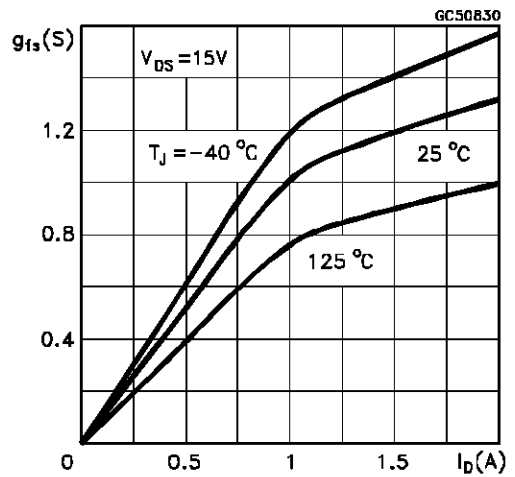
Output Characteristics



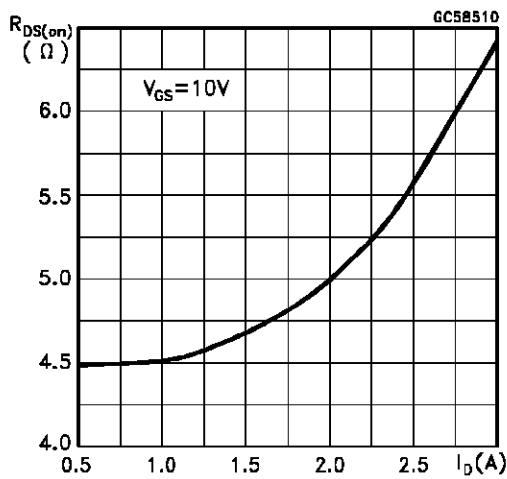
Transfer Characteristics



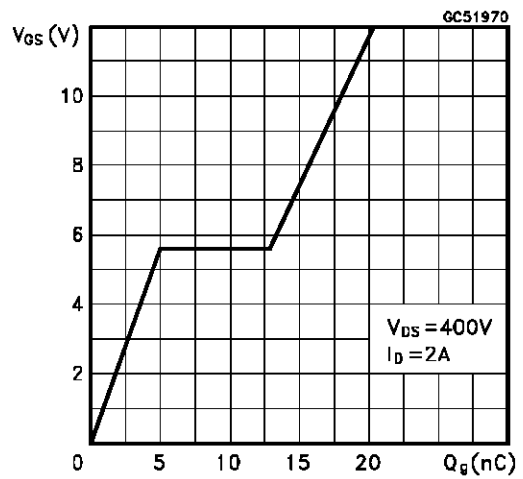
Transconductance



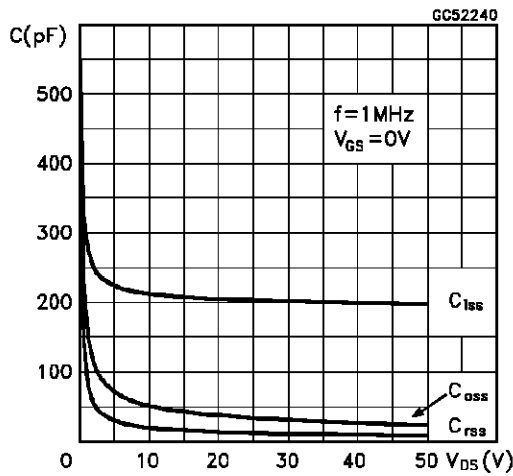
Static Drain-source On Resistance



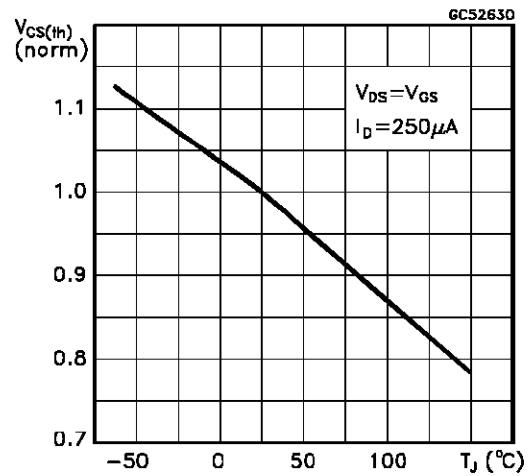
Gate Charge vs Gate-source Voltage



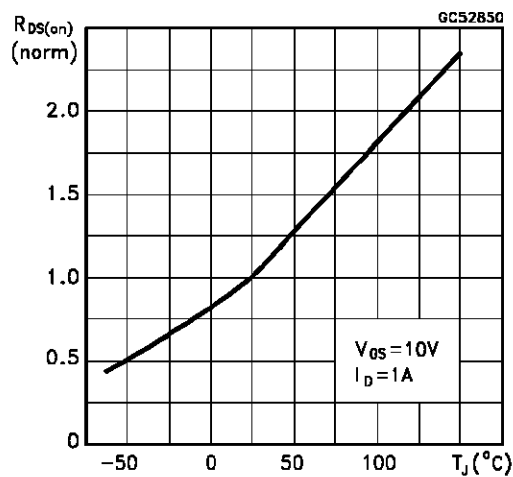
Capacitance Variations



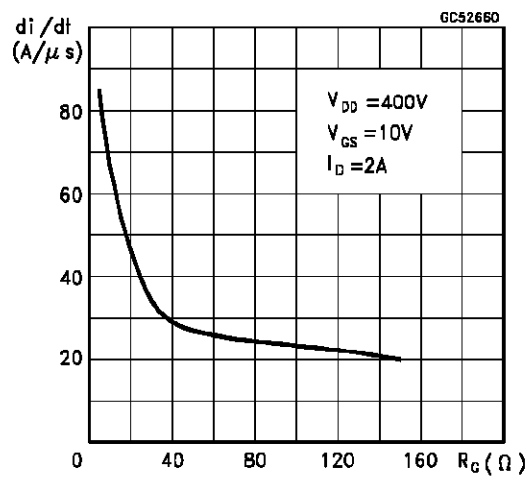
Normalized Gate Threshold Voltage vs Temperature



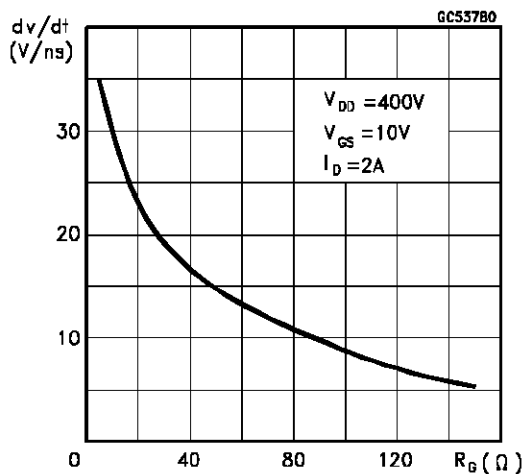
Normalized On Resistance vs Temperature



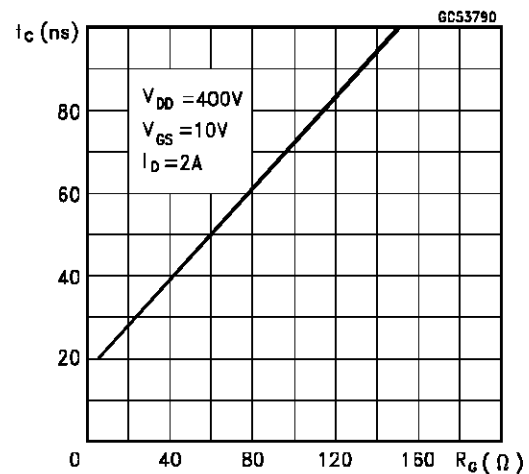
Turn-on Current Slope



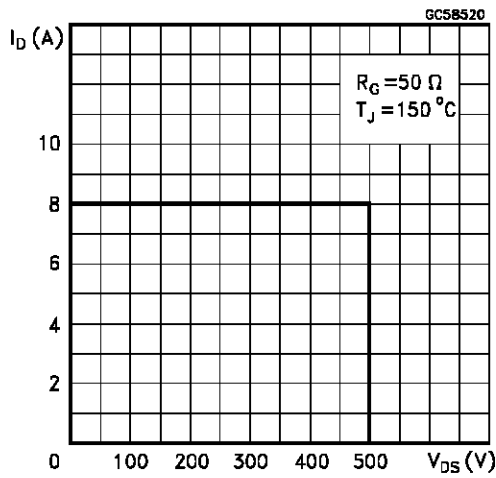
Turn-off Drain-source Voltage Slope



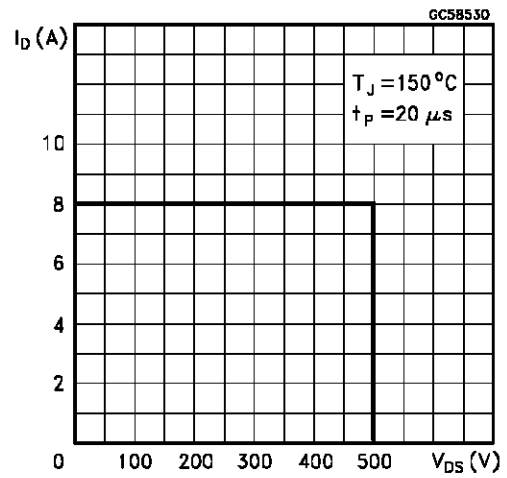
Cross-over Time



Switching Safe Operating Area



Accidental Overload Area



Source-drain Diode Forward Characteristics

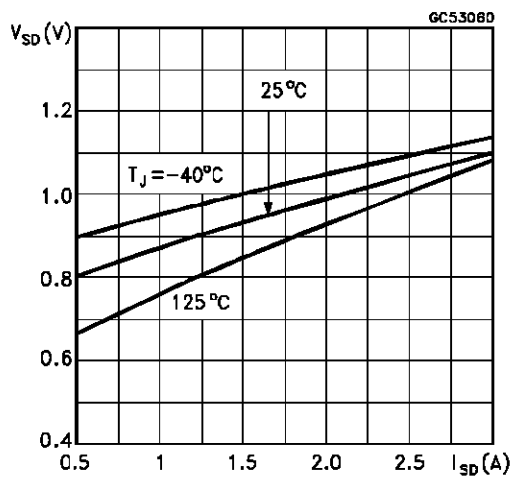


Fig. 1: Unclamped Inductive Load Test Circuits

Fig. 2: Unclamped Inductive Waveforms

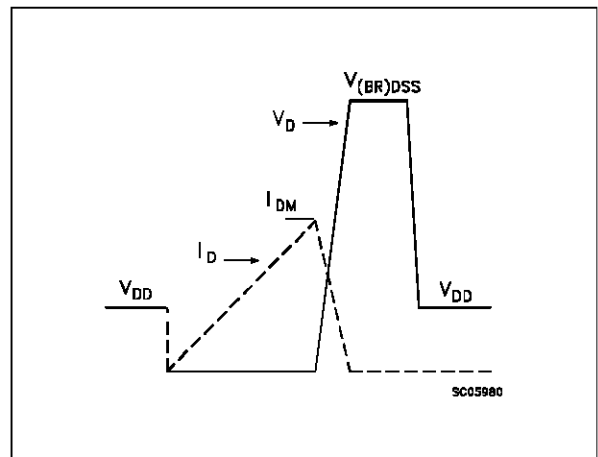
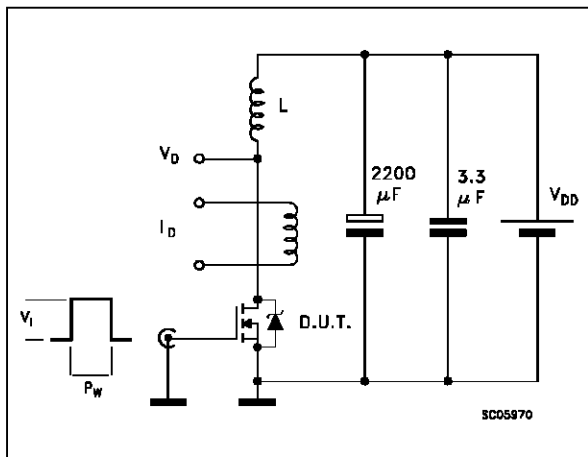


Fig. 3: Switching Times Test Circuits For Resistive Load



Fig. 4: Gate Charge Test Circuit

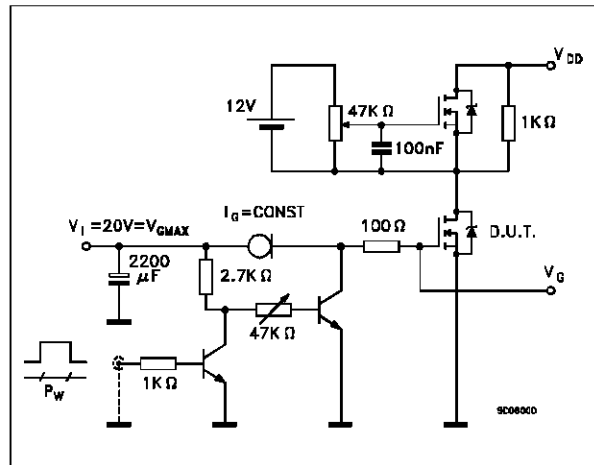


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



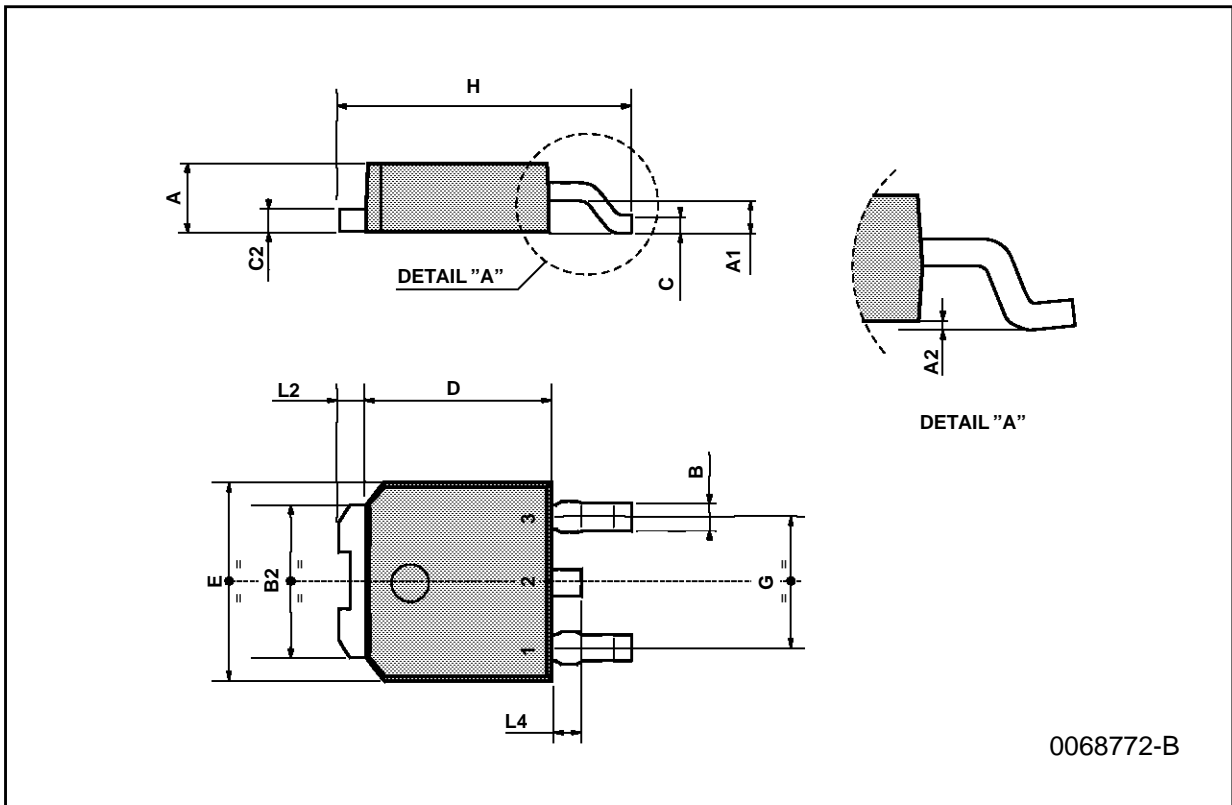
TO-251 (IPAK) MECHANICAL DATA

| DIM. | mm | | | inch | | |
|------|------|------|------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 2.2 | | 2.4 | 0.086 | | 0.094 |
| A1 | 0.9 | | 1.1 | 0.035 | | 0.043 |
| A3 | 0.7 | | 1.3 | 0.027 | | 0.051 |
| B | 0.64 | | 0.9 | 0.025 | | 0.031 |
| B2 | 5.2 | | 5.4 | 0.204 | | 0.212 |
| B3 | | | 0.85 | | | 0.033 |
| B5 | | 0.3 | | | 0.012 | |
| B6 | | | 0.95 | | | 0.037 |
| C | 0.45 | | 0.6 | 0.017 | | 0.023 |
| C2 | 0.48 | | 0.6 | 0.019 | | 0.023 |
| D | 6 | | 6.2 | 0.236 | | 0.244 |
| E | 6.4 | | 6.6 | 0.252 | | 0.260 |
| G | 4.4 | | 4.6 | 0.173 | | 0.181 |
| H | 15.9 | | 16.3 | 0.626 | | 0.641 |
| L | 9 | | 9.4 | 0.354 | | 0.370 |
| L1 | 0.8 | | 1.2 | 0.031 | | 0.047 |
| L2 | | 0.8 | 1 | | 0.031 | 0.039 |



TO-252 (DPAK) MECHANICAL DATA

| DIM. | mm | | | inch | | |
|------|------|------|------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 2.2 | | 2.4 | 0.086 | | 0.094 |
| A1 | 0.9 | | 1.1 | 0.035 | | 0.043 |
| A2 | 0.03 | | 0.23 | 0.001 | | 0.009 |
| B | 0.64 | | 0.9 | 0.025 | | 0.035 |
| B2 | 5.2 | | 5.4 | 0.204 | | 0.212 |
| C | 0.45 | | 0.6 | 0.017 | | 0.023 |
| C2 | 0.48 | | 0.6 | 0.019 | | 0.023 |
| D | 6 | | 6.2 | 0.236 | | 0.244 |
| E | 6.4 | | 6.6 | 0.252 | | 0.260 |
| G | 4.4 | | 4.6 | 0.173 | | 0.181 |
| H | 9.35 | | 10.1 | 0.368 | | 0.397 |
| L2 | | 0.8 | | | 0.031 | |
| L4 | 0.6 | | 1 | 0.023 | | 0.039 |



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